

BUK7275-100A

N-channel TrenchMOS standard level FET Rev. 02 — 17 June 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching

Motors, lamps and solenoids

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	21.7	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	89	W
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 13 \text{ A};$ $T_j = 175 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 12}}{\text{Figure 13}};$	-	-	187	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 13 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{see } \frac{\text{Figure } 13}}$	-	64	75	mΩ
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 14 \text{ A; } V_{sup} \leq 100 \text{ V;} \\ R_{GS} &= 50 \text{ \Omega; } V_{GS} = 10 \text{ V;} \\ T_{j(init)} &= 25 \text{ °C; } unclamped \end{split}$	-	-	100	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		G (EX)
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7275-100A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

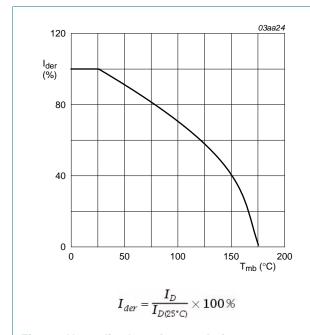
Limiting values

Limiting values Table 4.

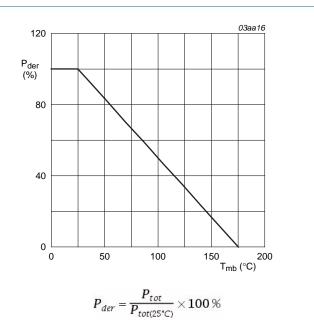
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _i ≥ 25 °C; T _i ≤ 175 °C		-	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	100	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>		-	-	21.7	Α
		$T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 10 ^{\circ}\text{V}; \text{see} \frac{\text{Figure 1}}{}$		-	-	15.4	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see Figure 3	<u>[1]</u>	-	-	87	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	89	W
T _{stg}	storage temperature			-55	-	175	°C
T _j	junction temperature			-55	-	175	°C
Source-drain	diode						
I _S	source current	T _{mb} = 25 °C		-	-	21.7	А
I _{SM}	peak source current	$t_p \le 10 \mu\text{s}; \text{ pulsed}; T_{mb} = 25 ^{\circ}\text{C}$		-	-	87	А
Avalanche rug	ggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 14 A; $V_{sup} \le$ 100 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	100	mJ

[1] Peak drain current is limited by chip, not package.



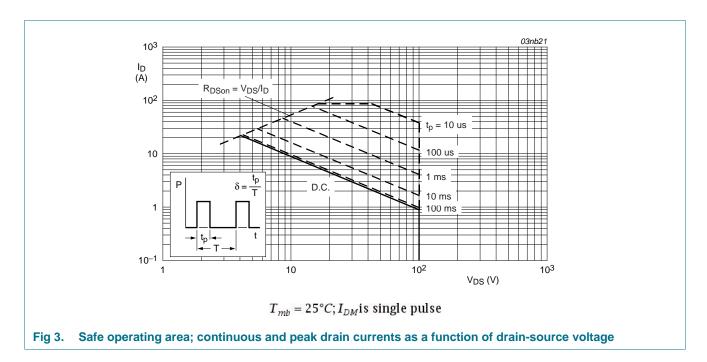
Normalized continuous drain current as a function of mounting base temperature



Normalized total power dissipation as a function of mounting base temperature

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; FR4 board	-	71.4	-	K/W

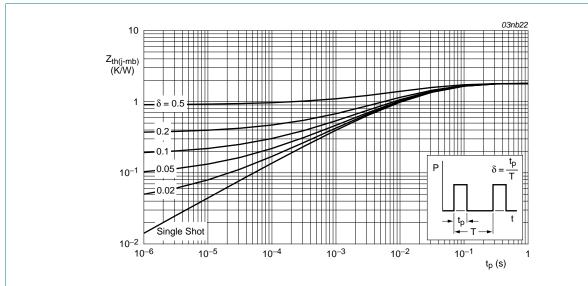


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 11	-	-	4.4	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 11</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 ^{\circ}\text{C}$	-	-	500	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I _{GSS}	gate leakage current	V _{DS} = 0 V; V _{GS} = 20 V; T _j = 25 °C	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 13 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	- 1	187	mΩ
		V_{GS} = 10 V; I_D = 13 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	64	75	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	910	1210	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	130	152	pF
C_{rss}	reverse transfer capacitance		-	80	107	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 2.2 \Omega; V_{GS} = 10 \text{ V};$	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega$; $T_j = 25 °C$	-	39	-	ns
t _{d(off)}	turn-off delay time		-	26	-	ns
t _f	fall time		-	24	-	ns
L _D	internal drain inductance	measured from drain lead from package to centre of die	-	2.5	-	nΗ
L _S	internal source inductance	measured from source lead from package to source bond pad	-	7.5	-	nΗ
Source-d	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 13 A; dI _S /dt = -100 A/μs; V _{GS} = -10 V; V _{DS} = 30 V; T _i = 25 °C	-	64	-	ns

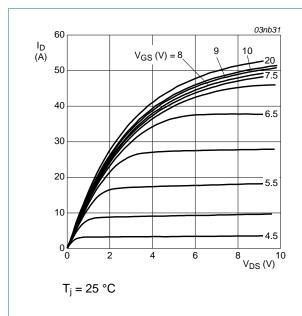


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

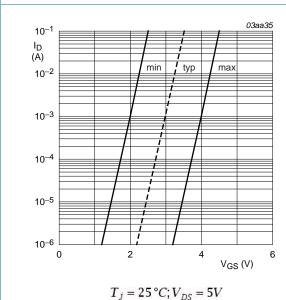
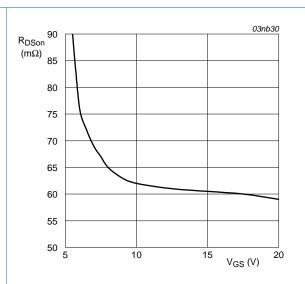


Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25^{\circ}C; I_D = 10A$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

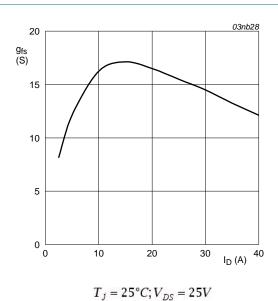


Fig 8. Forward transconductance as a function of drain current; typical values

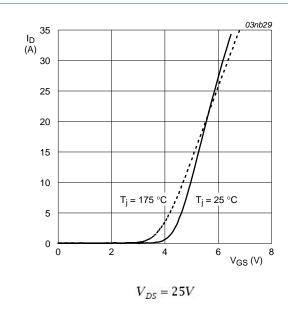
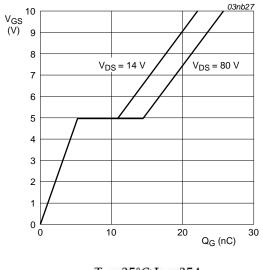


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j=25^{\circ}C; I_D=25A$

Fig 10. Gate-source voltage as a function of turn-on gate charge; typical values

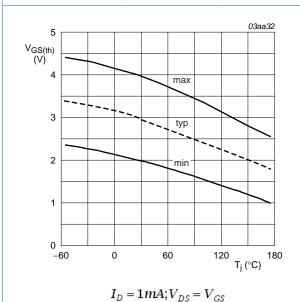


Fig 11. Gate-source threshold voltage as a function of junction temperature

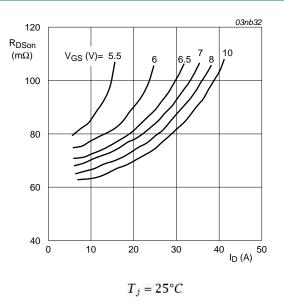


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

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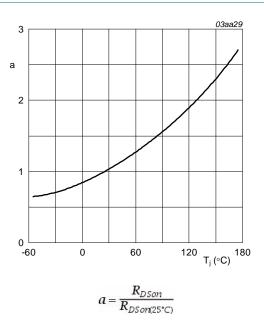


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

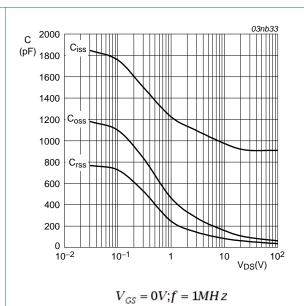


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

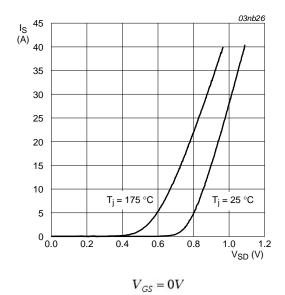


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

7. Package outline

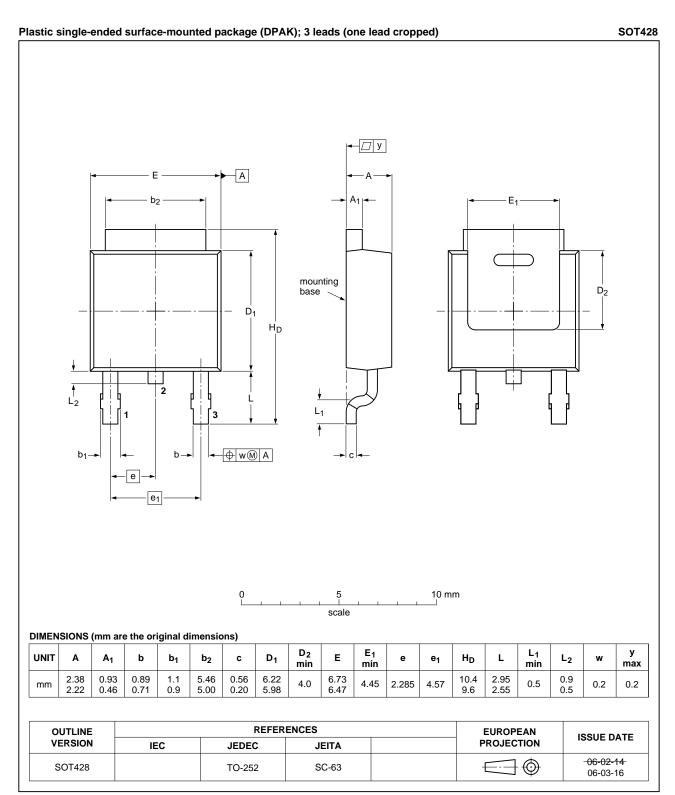


Fig 16. Package outline SOT428 (DPAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BUK7275-100A v.2	20100617	Product data sheet	-	BUK7275-100A v.1	
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelin of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. 				
BUK7275-100A v.1	20001025	Product Specification	-	-	

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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